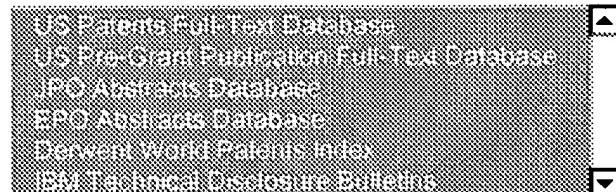


**WEST****Freeform Search****Database:****Term:****Display:** 50 **Documents in Display Format:** - Starting with Number 1**Generate:**  Hit List  Hit Count  Side by Side  Image**Search History****DATE:** Thursday, October 30, 2003 [Printable Copy](#) [Create Case](#)

<u>Set Name</u>	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u>
side by side			result set
<i>DB=USPT,PGPB,JPAB,EPAB,DWPI,TDBD; PLUR=YES; OP=OR</i>			
<u>L16</u>	l14 not l15	69	<u>L16</u>
<u>L15</u>	l8 same l14	24	<u>L15</u>
<u>L14</u>	l6 near10 l11	93	<u>L14</u>
<u>L13</u>	l5 near10 l11	5	<u>L13</u>
<u>L12</u>	l9 near10 l11	4	<u>L12</u>
<u>L11</u>	rate or growthrate	1865502	<u>L11</u>
<u>L10</u>	l7 same l9	85	<u>L10</u>
<u>L9</u>	l6 adj5 l8	214	<u>L9</u>
<u>L8</u>	buffer	618739	<u>L8</u>
<u>L7</u>	rate or thick\$4	3387419	<u>L7</u>
<u>L6</u>	l1 or l5	3066	<u>L6</u>
<u>L5</u>	l4 adj3 nitride	769	<u>L5</u>
<u>L4</u>	aluminum adj gallium	8834	<u>L4</u>
<u>L3</u>	l1 or l2	991486	<u>L3</u>
<u>L2</u>	gallium adh aluminum	990594	<u>L2</u>
<u>L1</u>	algan or gaaln	2700	<u>L1</u>

END OF SEARCH HISTORY

**WEST**

End of Result Set

 [Generate Collection](#) 

L15: Entry 24 of 24

File: DWPI

Mar 15, 2002

DERWENT-ACC-NO: 2002-447374

DERWENT-WEEK: 200248

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**TITLE:** Formation of nitride group semiconductor layer for semiconductor element, involves forming semiconductor layer of mixed nitride of aluminum, boron, indium, thallium and gallium, on buffer layer formed on substrate

**Basic Abstract Text (1):**

NOVELTY - The buffer layer (2) comprising aluminum gallium nitride is grown on a substrate (1), at a growth rate of more than 7 Angstrom /second. A nitride group semiconductor layer (3) comprising a mixed nitride of aluminum, boron, indium, thallium and gallium, is grown on the buffer layer.

**Equivalent Abstract Text (1):**

NOVELTY - The buffer layer (2) comprising aluminum gallium nitride is grown on a substrate (1), at a growth rate of more than 7 Angstrom /second. A nitride group semiconductor layer (3) comprising a mixed nitride of aluminum, boron, indium, thallium and gallium, is grown on the buffer layer.